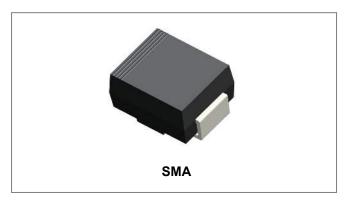


RoHS



S1A THRU S1M 1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMA molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: AnyWeight: 0.06 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Type Number	Symbol	S1A	S1B	S1D	S1G	S1J	S1K	S1M	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average Rectified Output Current @T _L = 100°C	lo	1.0			Α				
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30			А				
Forward Voltage @ I _F = 1.0 A	V _F				1.10				V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 125°C	I _{RM}				5.0 200				μA
Reverse Recovery Time(Note1)	t _{rr}				2.5				μS
Typical Junction Capacitance(Note2)	CJ	15				pF			
Typical Thermal Resistance Junction to Lead (Note 3)	R _{θJL}				30				°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-65 to +175				°C			

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Mounted on P.C.B.with 8.0mm² land areas.
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 sales@ smc-diodes.com







Ratings and Characteristics Curves

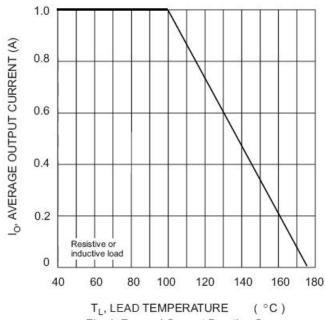
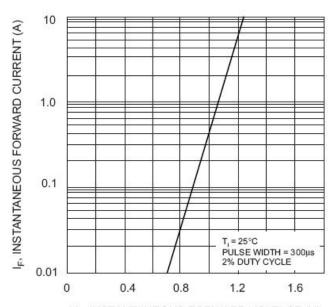
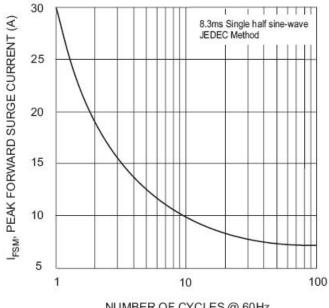


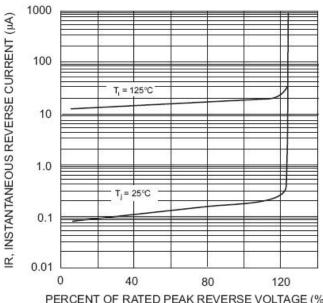
Fig. 1 Forward Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics



NUMBER OF CYCLES @ 60Hz Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 4 Typical Reverse Characteristics

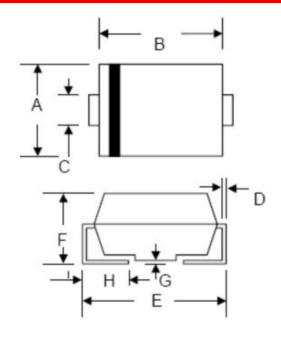
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Mechanical Dimensions SMA



SYMBOL	Millir	meters	Inches		
STIVIBUL	Min.	Max.	Min.	Max.	
Α	2.40	2.84	0.094	0.112	
В	3.99	4.75	0.157	0.187	
С	1.05	1.70	0.041	0.067	
D	0.15	0.51	0.006	0.020	
Е	4.80	5.66	0.189	0.223	
F	1.90	2.95	0.075	0.116	
G	0.05	0.203	0.002	0.008	
Н	0.76	1.52	0.030	0.600	

Ordering Information

Device	Package	Shipping
S1A-S1M	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 S1A
 = Type Number

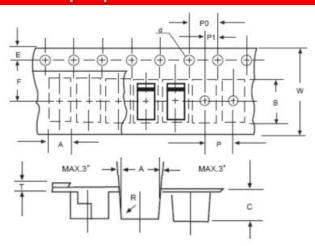
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification SMA



SYMBOL	Millimeters			
	Min.	Max.		
Α	2.97	3.17		
В	5.70	5.90		
С	2.32	2.52		
d	1.40	1.60		
E	1.40	1.60		
F	5.60	5.70		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
Т	0.25	0.35		
W	11.80	12.20		

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